Unit: mm

TOSHIBA Field Effect Transistor with Built-in Schottky Barrier Diode Silicon N-Channel MOS Type (U-MOS V-H)

TPC8A04-H

High Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

Built-in schottky barrier diode
 Low forward voltage: V_{DSF} = -0.6 V (max)

· High-speed switching

• Small gate charge: Q_{SW} = 13 nC (typ.)

• Low drain-source ON-resistance: $R_{DS (ON)} = 2.6 \text{ m}\Omega \text{ (typ.)}$

• High forward transfer admittance: |Yfs| = 62 S (typ.)

• Low leakage current: $I_{DSS} = 100 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$

• Enhancement mode: V_{th} = 1.3 to 2.3 V (V_{DS} = 10 V, I_D = 1 mA)

Absolute Maximum Ratings (Ta = 25°C)

Characte	eristic	Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Drain-gate voltage (R	$R_{GS} = 20 \text{ k}\Omega$	V_{DGR}	30	V
Gate-source voltage		V _{GSS}	±20	V
Drain current	DC (Note 1)	ID	18	Α
Drain current	Pulsed (Note 1)	I _{DP}	72	A
Drain power dissipation	on (t = 10 s) (Note 2a)	P_{D}	1.9	W
Drain power dissipation	on (t = 10 s) (Note 2b)	P _D	1.0	W
Single-pulse avalanch	he energy (Note 3)	E _{AS}	211	mJ
Avalanche current		I _{AR}	18	Α
Repetitive avalanche	energy c = 25°C) (Note 4)	E _{AR}	0.082	mJ
Channel temperature		T _{ch}	150	°C
Storage temperature	range	T _{stg}	-55 to 150	°C

0.595TVP 1.27

1, 2, 3 SOURCE
4 GATE
5, 6, 7, 8 DRAIN

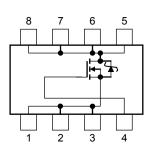
JEDEC —

JEITA —

TOSHIBA 2-6J1B

Weight: 0.085g (typ.)

Circuit Configuration



Note: For Notes 1 to 4, refer to the next page.

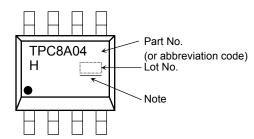
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient $(t=10 \; s) \eqno(Note \; 2a)$	R _{th (ch-a)}	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	125	°C/W

Marking (Note 5)



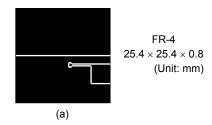
Note : A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

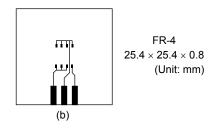
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)

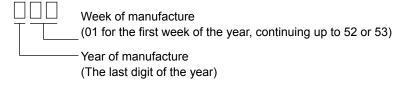




Note 3: $V_{DD}=24~V,~T_{ch}=25^{\circ}C$ (initial), $L=500~\mu H,~R_{G}=25~\Omega,~I_{AR}=18~A$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: * Weekly code: (Three digits)



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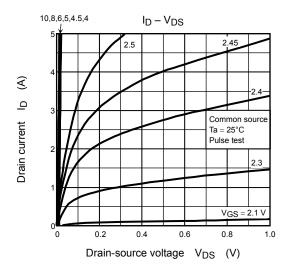
Electrical Characteristics (Ta = 25°C)

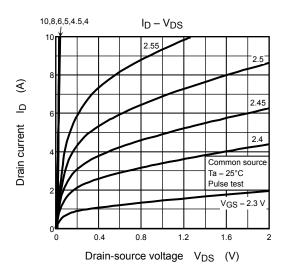
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cut-off curre	ent	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V		_	100	μА
Drain-source breakdown voltage		V _{(BR)DSS}	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V
Drain-source brea	akdown voltage	V _{(BR) DSX}	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	30 — — — — — — — — — — — — — — — — — — —		V
Gate threshold vo	oltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.3	.3 — 2.3		V
Drain-source ON	rociotopo	P== (==)	V _{GS} = 4.5 V, I _D = 9 A	_	3.2	4.5	- mΩ
Drain-source ON	-resistance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 9 A		2.6	3.6	
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 9 A	31	62	_	S
Input capacitance	•	C _{iss}			4400	5700	pF
Reverse transfer	capacitance	C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		180	270	
Output capacitance		Coss			990	_	
Gate resistance		rg	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 5 \text{ MHz}$	_	1.0	1.0 1.5	
Switching time	Rise time	t _r	VGS 0 V	_	4.5	_	ns
	Turn-on time	t _{on}		_	13.2	_	
	Fall time	t _f		_	7.7	_	
	Turn-off time	t _{off}	$V_{DD} \approx 15 \text{ V}$ Duty $\leq 1\%$, $t_W = 10 \mu\text{s}$	_	54	_	
Total gate charge		Qq	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 18 \text{ A}$		56	_	
(gate-source plus	e-source plus gate-drain)		$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 18 \text{ A}$		29	_	
Gate-source charge 1		Q _{gs1}		_	12	_	nC
Gate-drain ("Miller") charge		Q _{gd}	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 18 \text{ A}$		7.0	_	-
Gate switch charge		Q _{SW}]	_	13	_	

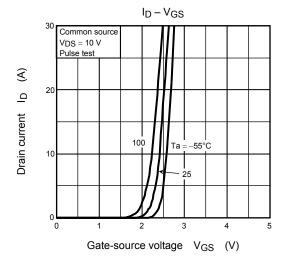
Source-Drain Ratings and Characteristics (Ta = 25°C)

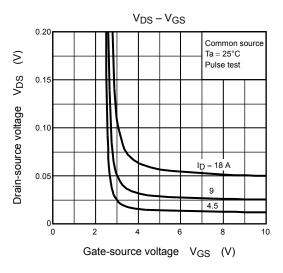
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I _{DRP}	_	_	_	72	Α
Forward voltage (diode)		V_{DSF}	I _{DR} = 1 A, V _{GS} = 0 V	_	- 0.4	- 0.6	V	
			I _{DR} = 18 A, V _{GS} = 0 V	_	_	- 1.2	V	

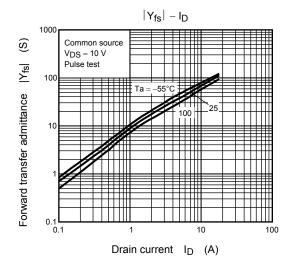
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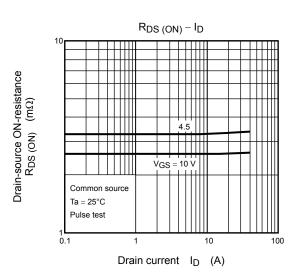


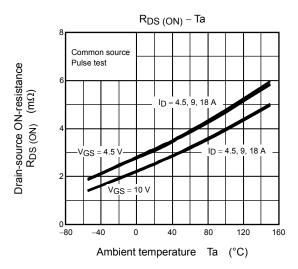


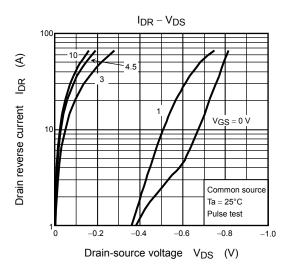


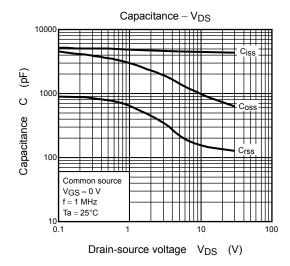


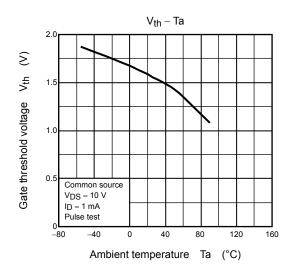


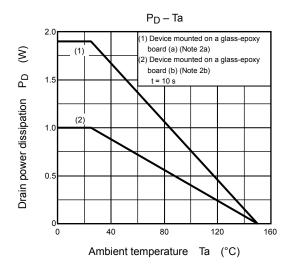


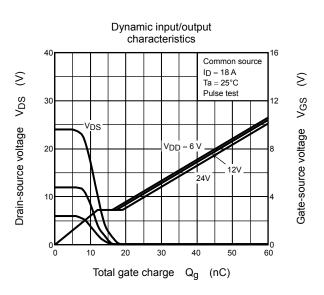


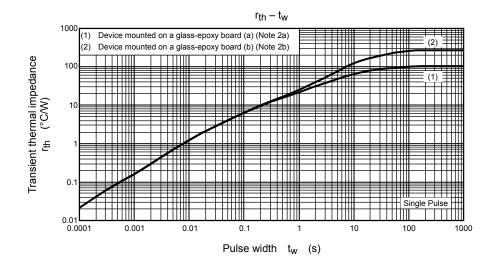


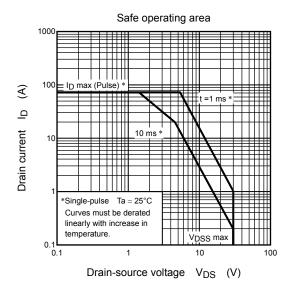


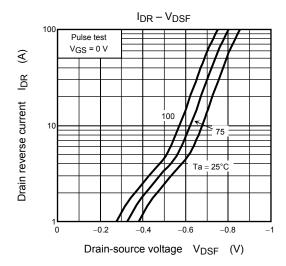


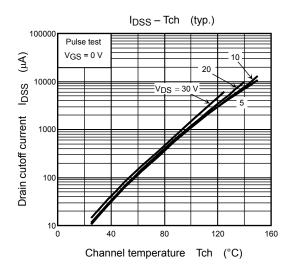


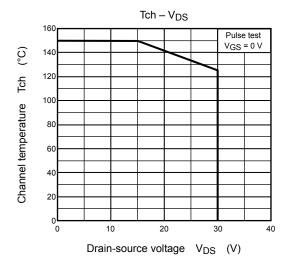












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